Abstract

Silicon wafer and manufacturing method thereof

To provide a manufacturing method of a silicon wafer, with which a desired strength and electric resistance of a semiconductor device can be obtained.

A non-oxidizing heat treatment for oxygen out-diffusion is performed on an intermediate 10 so as to manufacture a silicon wafer 1. The heat treatment for oxygen out-diffusion is a heat treatment wherein the desired amount of oxygen is discharged from the surface layer of the silicon substrate to the outside of the intermediate 10. By this heat treatment for oxygen out-diffusion, the surface layer 3 having a low oxygen content is formed on the silicon substrate 11. Here, the heat treatment of the silicon substrate 11 is performed through the oxide film 12.

Fig. 2